

## 20V P-Channel Power MOSFET

**UM2301S SOT23-3**

**UM2301P SOT323**

### General Description

The UM2301 is a low threshold P-channel MOSFET, have extremely low on-resistance. This benefit provides the designer with an extremely efficient device for use in battery and load management applications. The device uses a space-saving, small-outline SOT23-3 or SOT323 package.

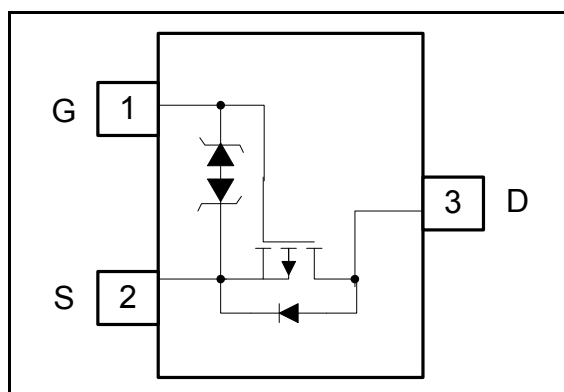
### Applications

- Battery Packs
- Battery-powered Portable Equipment
- Cellular and Cordless Telephones

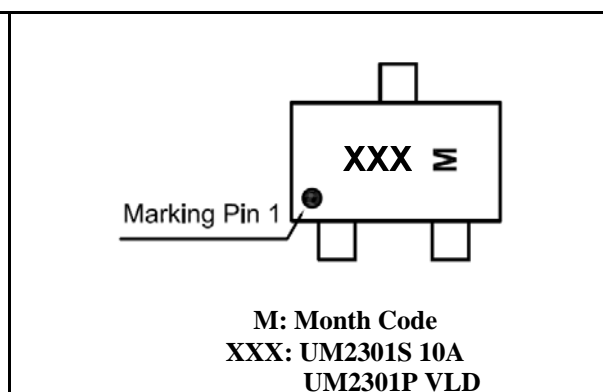
### Features

- Drain-Source Voltage(max): -20V
- Low On-Resistance:  
200mΩ@V<sub>GS</sub>=-4.5V  
250mΩ@V<sub>GS</sub>=-2.5V
- Continuous Drain Current(max):  
-1.5A@25°C(SOT23-3)  
-1.1A@25°C(SOT323)

### Pin Configurations



### Top View



### Ordering Information

Part Number	Packaging Type	Marking Code	Shipping Qty
UM2301S	SOT23-3	10A	3000pcs/7 Inch Tape & Reel
UM2301P	SOT323	VLD	

### Absolute Maximum Ratings

Symbol	Parameter	Value	Units
V <sub>DSS</sub>	Drain-Source voltage	-20	V
V <sub>GS</sub>	Gate-Source voltage	±8	V
I <sub>D</sub>	Continuous Drain Current (5s)	SOT23-3	-1.5
		SOT323	-1.1
I <sub>DP</sub>	Drain Current Pulsed	-5	A

		(Pulse Width $\leq 10\mu\text{s}$ , Duty Cycle $\leq 1\%$ )		
$P_D$	Power Dissipation	SOT23-3	0.86	W
		SOT323	0.5	
$T_J$	Junction Temperature		-55~150	$^{\circ}\text{C}$
$T_{\text{stg}}$	Storage Temperature		-55~150	$^{\circ}\text{C}$
$R_{\theta\text{JA}}$	Thermal Resistance, Junction-to-Ambient ( $\leq 5\text{s}$ )	SOT23-3	145	$^{\circ}\text{C}/\text{W}$
		SOT323	250	
ESD	ESD Method 3015.8		2000	V

**Electrical Characteristics ( $T_J=25^{\circ}\text{C}$ , Unless otherwise noted)**

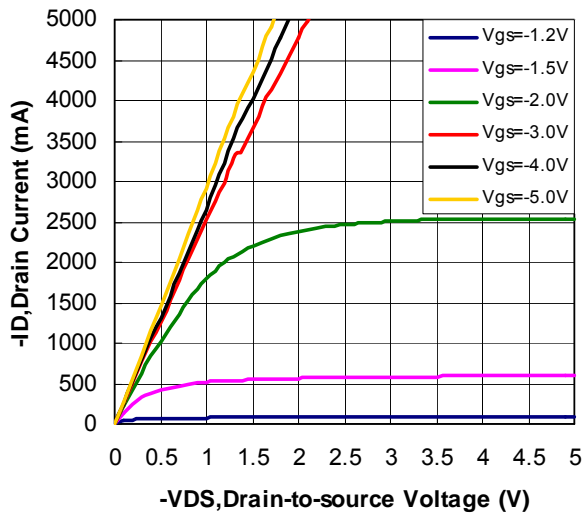
Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
$BV_{\text{DSS}}$	Drain to Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}$ , $I_{\text{D}}=-250\mu\text{A}$	-20			V
$I_{\text{DSS}}$	Zero Gate Voltage Drain Current	$V_{\text{DS}}=-20\text{V}$ , $V_{\text{GS}}=0\text{V}$			-0.1	$\mu\text{A}$
$I_{\text{GSS}}$	Gate-to-Source Leakage Current	$V_{\text{GS}}=\pm 8\text{V}$ , $V_{\text{DS}}=0\text{V}$			$\pm 10$	$\mu\text{A}$
<b>On Characteristics</b>						
$R_{\text{DS(ON)}}$	Static Drain-to-Source On-Resistance <sup>a</sup>	$V_{\text{GS}}=-4.5\text{V}$ , $I_{\text{D}}=-1.0\text{A}$		200	350	m $\Omega$
		$V_{\text{GS}}=-2.5\text{V}$ , $I_{\text{D}}=-1.0\text{A}$		250	400	
$V_{\text{GS(TH)}}$	Gate-Source Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}$ , $I_{\text{D}}=-250\mu\text{A}$	-0.4	-0.6	-1	V
$g_{\text{fs}}$	Forward Transconductance <sup>a</sup>	$V_{\text{DS}}=-5\text{V}$ , $I_{\text{D}}=-2.0\text{A}$		4.5		S
<b>Dynamic Characteristics<sup>b</sup></b>						
$C_{\text{iss}}$	Input Capacitance	$V_{\text{GS}}=0\text{V}$ , $V_{\text{DS}}=-10\text{V}$ , $f=1.0\text{MHz}$		405		pF
$C_{\text{oss}}$	Output Capacitance			150		
$C_{\text{rss}}$	Reverse Transfer Capacitance			55		
<b>Switching Characteristics<sup>b</sup></b>						
$t_{\text{d(on)}}$	Turn-on Delay Time	$V_{\text{DD}}=-10\text{V}$ , $R_{\text{L}}=10\Omega$ , $I_{\text{D}}=-1\text{A}$ , $V_{\text{GEN}}=-4.5\text{V}$ , $R_{\text{G}}=1\Omega$		11	20	ns
$t_{\text{r}}$	Rise Time			35	60	
$t_{\text{d(off)}}$	Turn-off Delay Time			80	150	
$t_{\text{f}}$	Fall Time			50	90	
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$V_{\text{SD}}$	Forward Diode Voltage	$I_{\text{S}}=-0.7\text{A}$		-0.8	-1.2	V

a: Pulse test: pulse width  $\leq 300\mu\text{s}$ , duty cycle  $\leq 2\%$ .

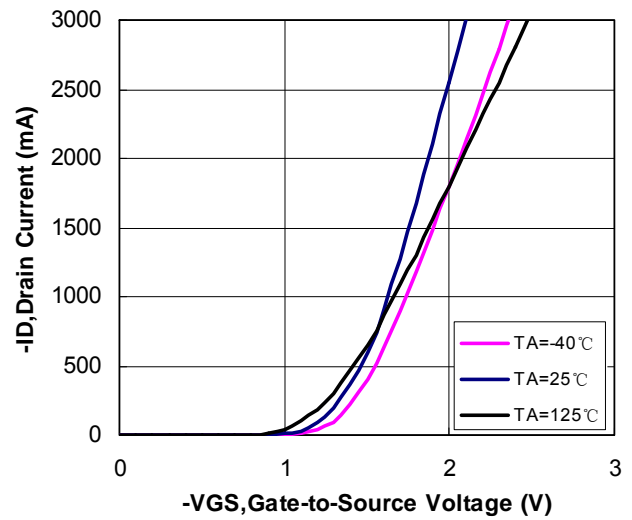
b: Guaranteed by design, not subject to production testing.

## Typical Characteristics ( $T_J=25^\circ\text{C}$ , Unless otherwise noted)

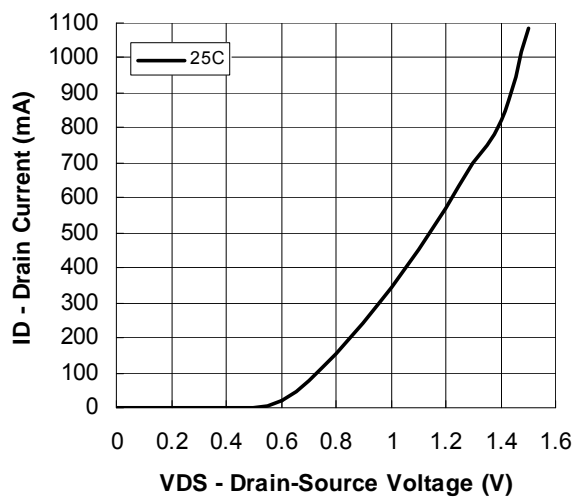
### Output Characteristics



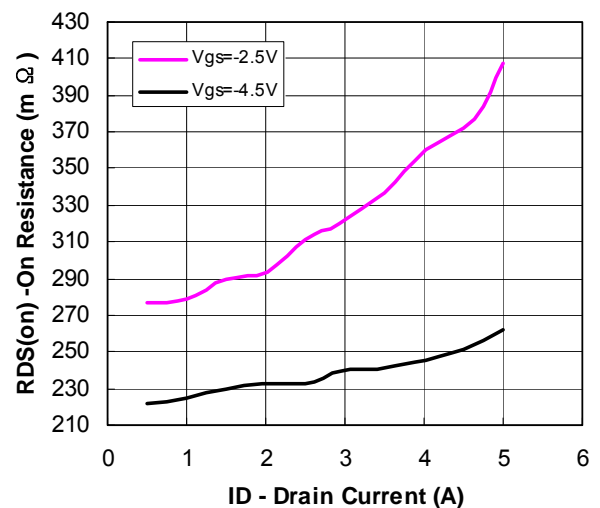
### Transfer Characteristics



### Source-Drain Diode Forward Voltage

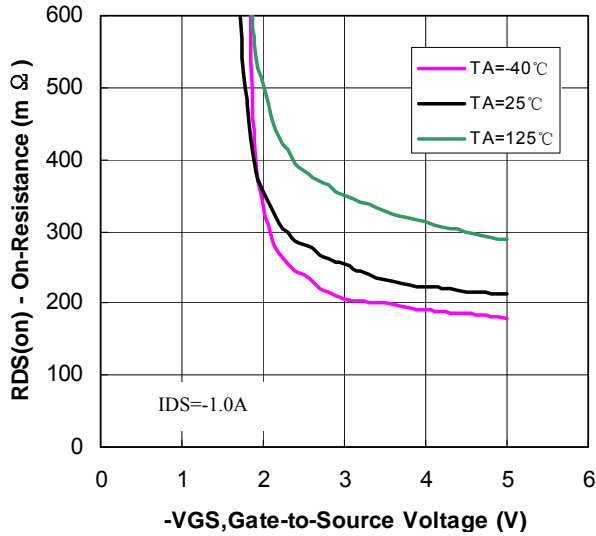


### On Resistance vs. Drain Current

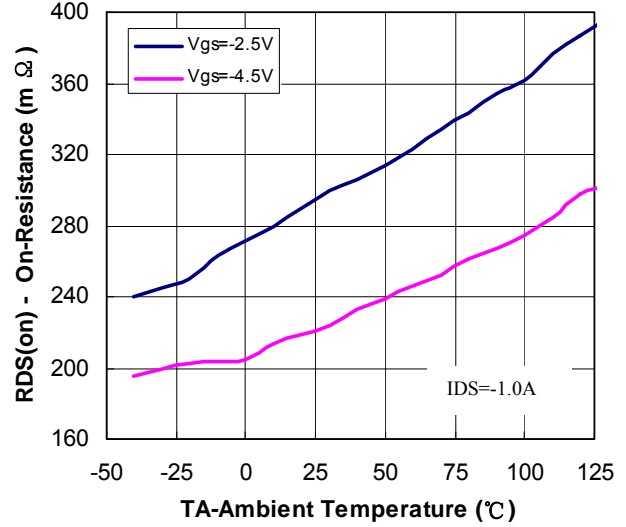


**Typical Characteristics (T<sub>J</sub>=25°C, Unless otherwise noted)**

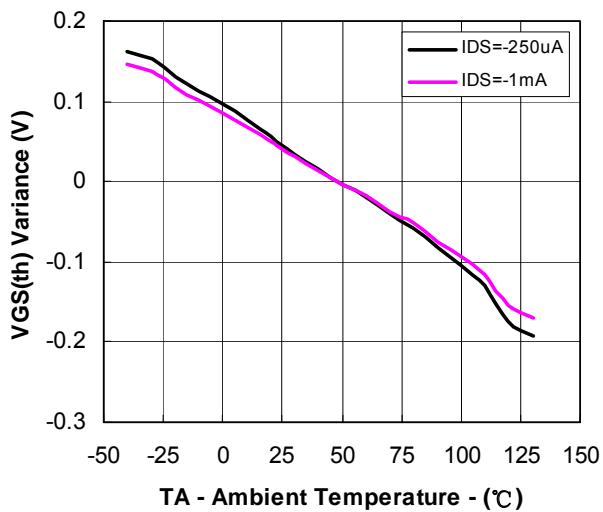
**On-Resistance vs. Gate-to-Source Voltage**



**On-Resistance vs. Ambient Temperature**



**Threshold Voltage vs. Ambient Temperature**



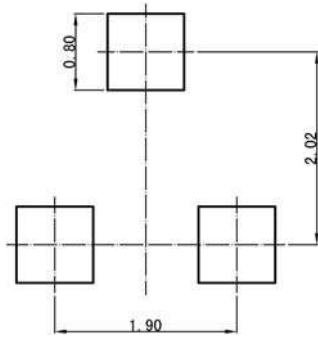
## Package Information

### UM2301S SOT23-3

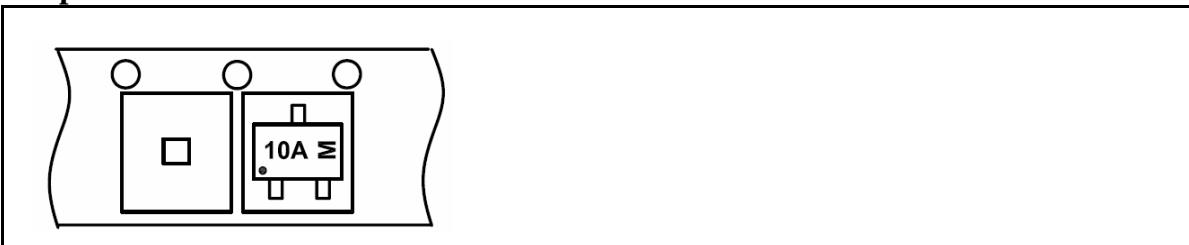
#### Outline Drawing

DIMENSIONS				
Symbol	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950REF		0.037REF	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.600	0.012	0.024
$\theta$	0°	8°	0°	8°

#### Land Pattern

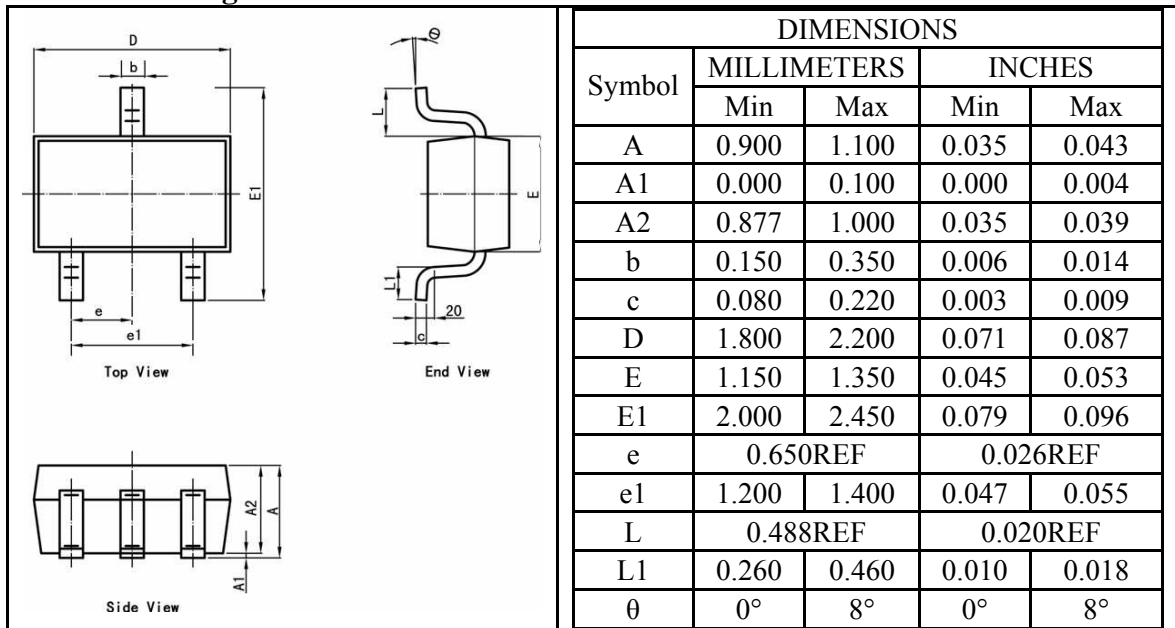
	<p>NOTES:</p> <ol style="list-style-type: none"> <li>Compound dimension: 2.92×1.60;</li> <li>Unit: mm;</li> <li>General tolerance ±0.05mm unless otherwise specified;</li> <li>The layout is just for reference.</li> </ol>
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#### Tape and Reel Orientation

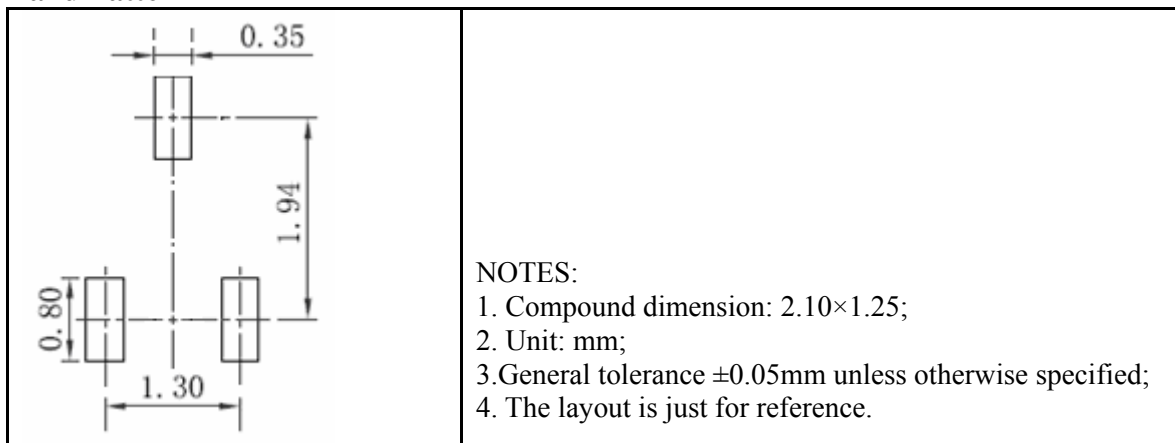


## UM2301P SOT323

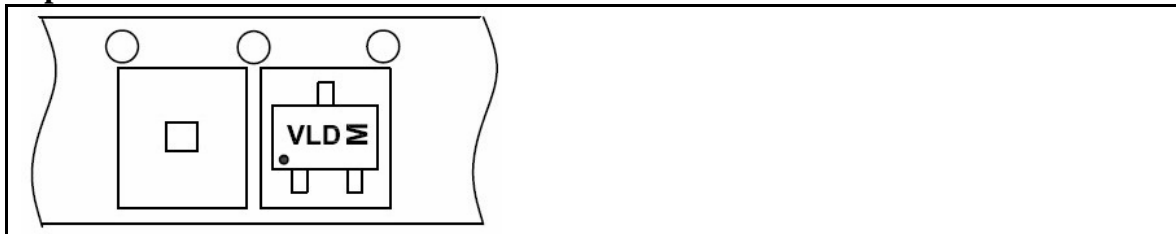
### Outline Drawing



### Land Pattern



### Tape and Reel Orientation



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